# **2SA0879** (2SA879)

## Silicon PNP epitaxial planar type

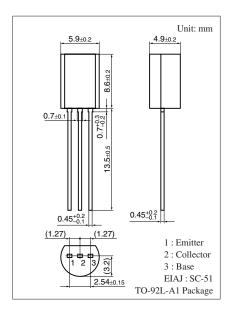
For general amplification Complementary to 2SC1573

#### ■ Features

ullet High collector-emitter voltage (Base open)  $V_{CEO}$ 

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-250	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-200	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_{C}$	-70	mA
Peak collector current	$I_{CP}$	-100	mA
Collector power dissipation	P <sub>C</sub>	1	W
Junction temperature	$T_{j}$	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C



### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

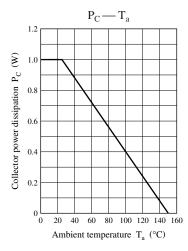
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -100 \ \mu A, I_B = 0$	-200			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -1  \mu A,  I_C = 0$	-5			V
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = -10 \text{ V}, \ I_{C} = -5 \text{ mA}$	60		220	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -50 \text{ mA}, I_B = -5 \text{ mA}$			-1.5	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	50	80		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		5	10	pF
(Common base, input open circuited)						

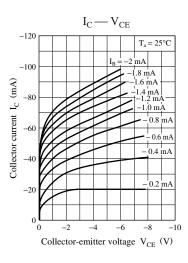
 $Note) \ 1. \ Measuring \ methods \ are \ based \ on \ JAPANESE \ INDUSTRIAL \ STANDARD \ JIS \ C \ 7030 \ measuring \ methods \ for \ transistors.$ 

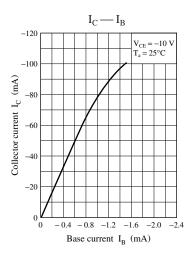
#### 2. \*: Rank classification

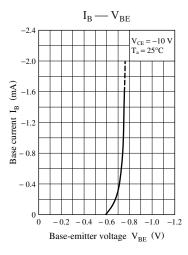
Rank	Q	R
$h_{ m FE}$	60 to 150	100 to 220

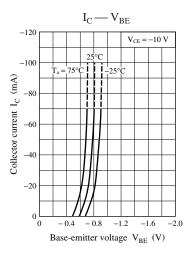
Note) The part number in the parenthesis shows conventional part number.

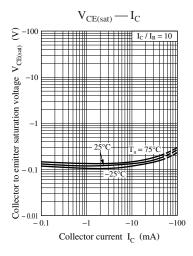


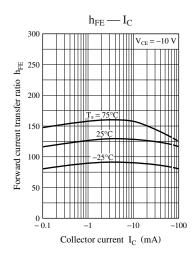


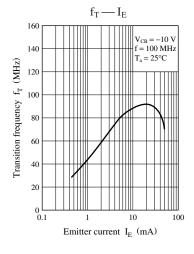


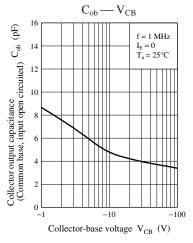


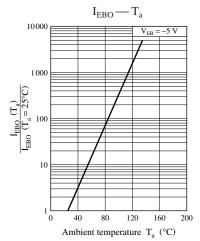


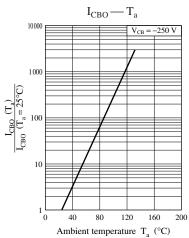


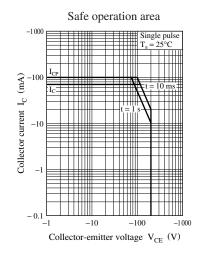












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